

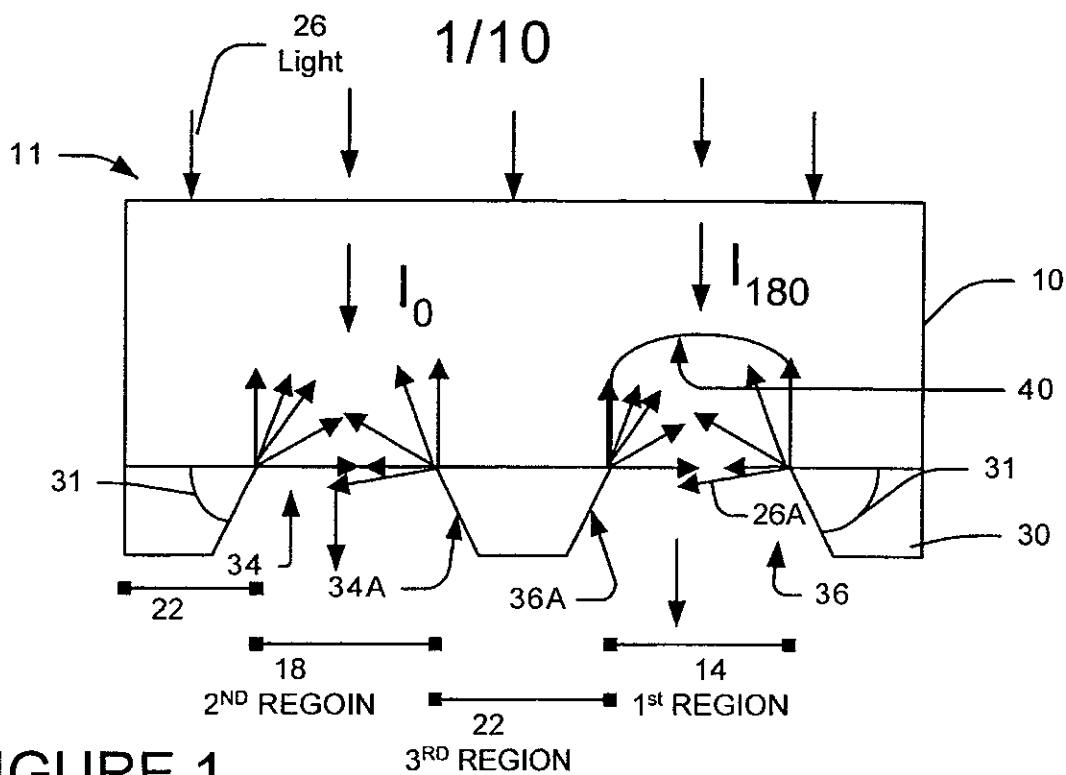


FIGURE 1

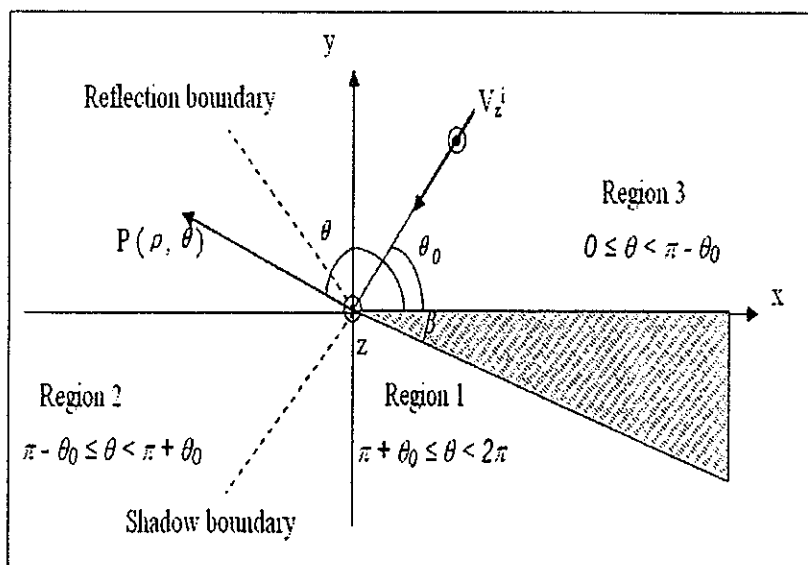


FIGURE 2

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FIG. 3A

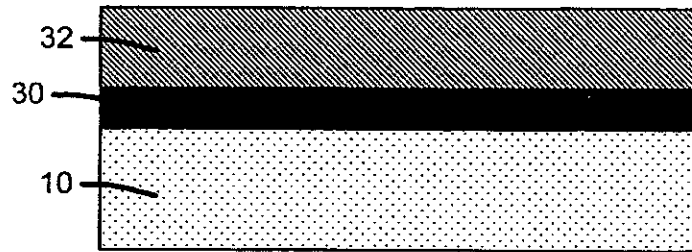


FIG. 3B

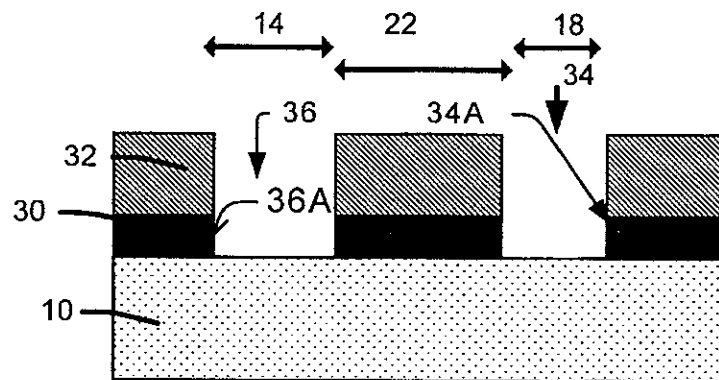


FIG. 3C

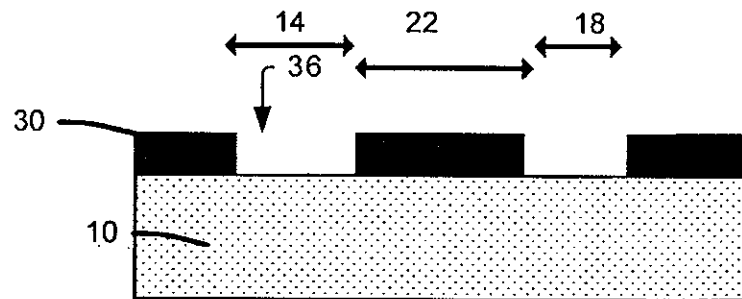
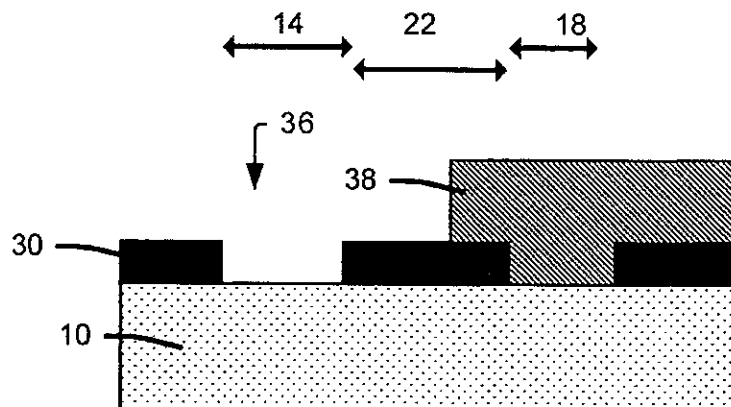


FIG. 3D



A cross-sectional view of a substrate 10 with a trench 30. A layer 34 is formed on the top surface of the substrate 10. The layer 34 has a thickness d_{etch} . The trench 30 is formed in the substrate 10, and the layer 34 is etched away from the bottom of the trench 30. The etching process is indicated by arrow 36, and the resulting etched surface is labeled 40.

A cross-sectional diagram of a substrate 10 with a top layer 30. Two recesses are formed in the top layer. The first recess has a depth indicated by arrow 36 and contains a feature 40. The second recess has a depth indicated by arrow 34 and contains a feature 44. A double-headed vertical arrow labeled d_{etch} indicates the etch depth from the original surface level to the bottom of the second recess. Labels 36A and 34A point to the side walls of the first and second recesses, respectively.

FIG. 3G

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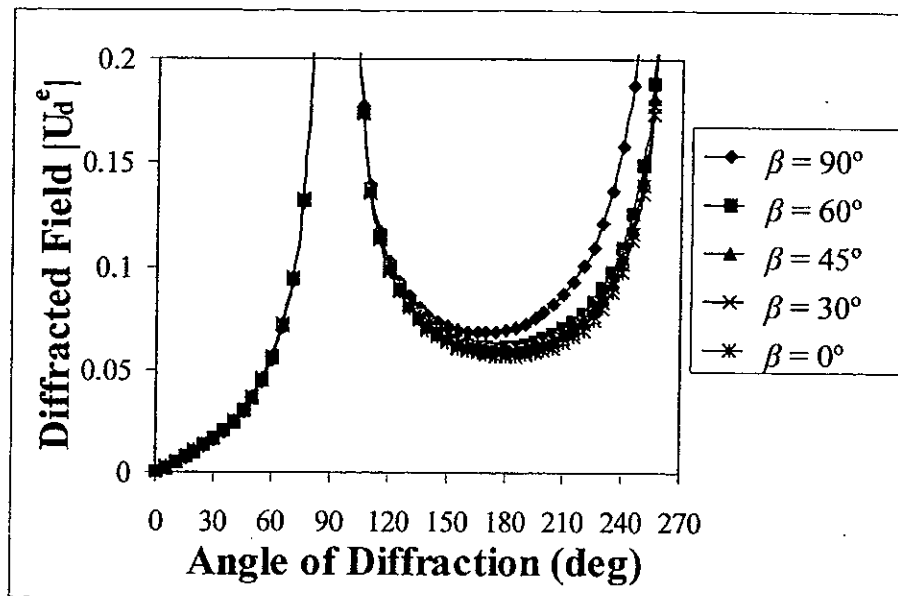


FIGURE 4A

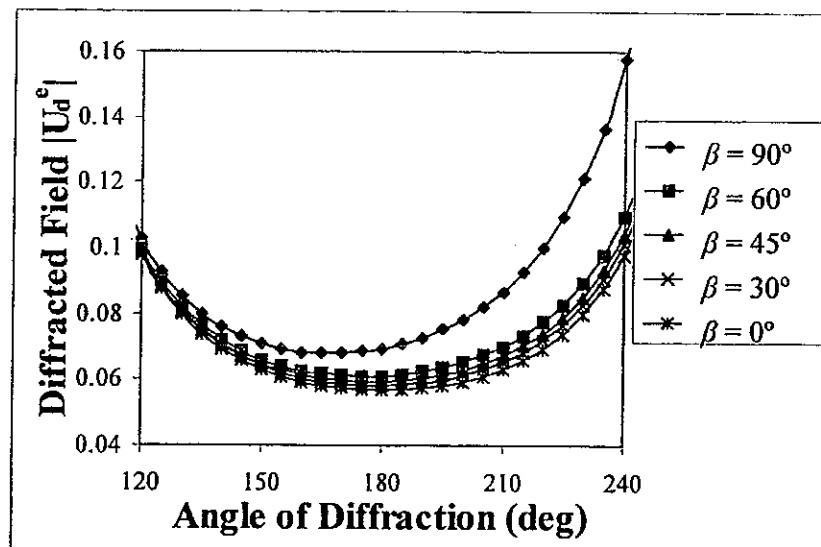


FIGURE 4B

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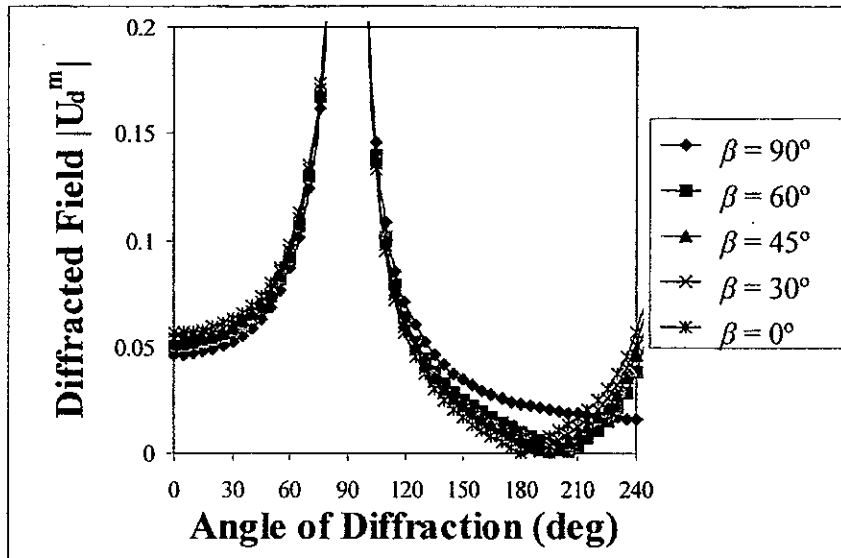


FIGURE 5A

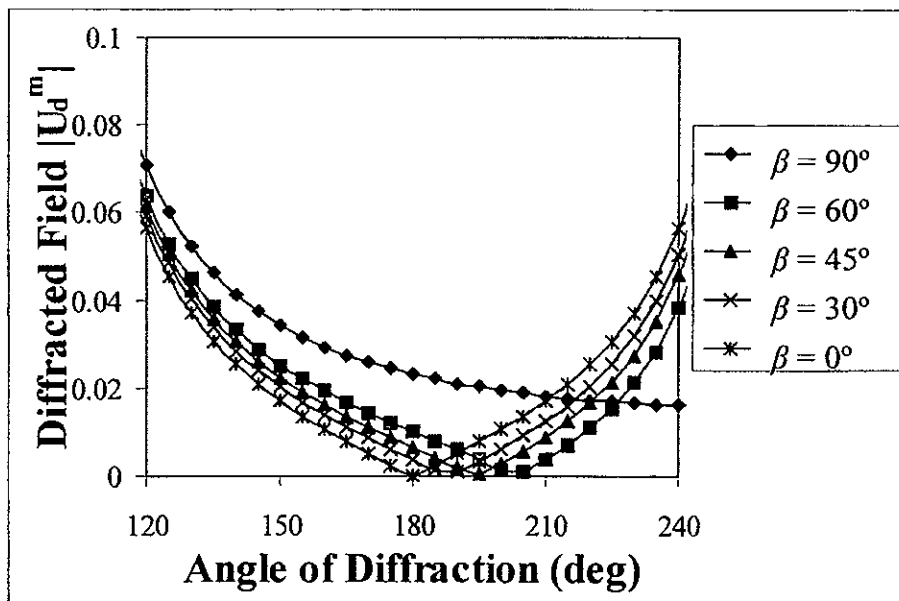


FIGURE 5B

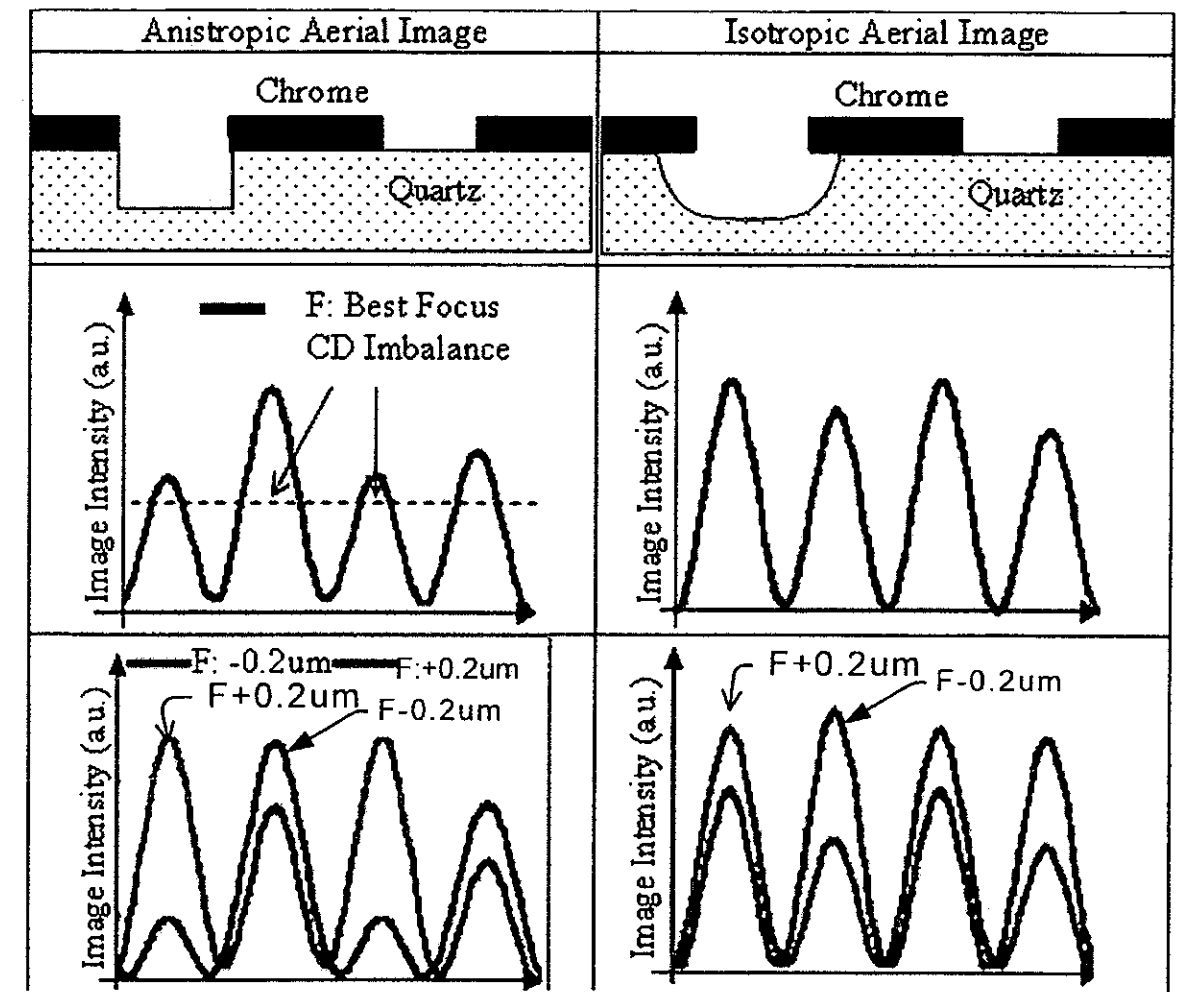


FIGURE 6A

FIGURE 6B

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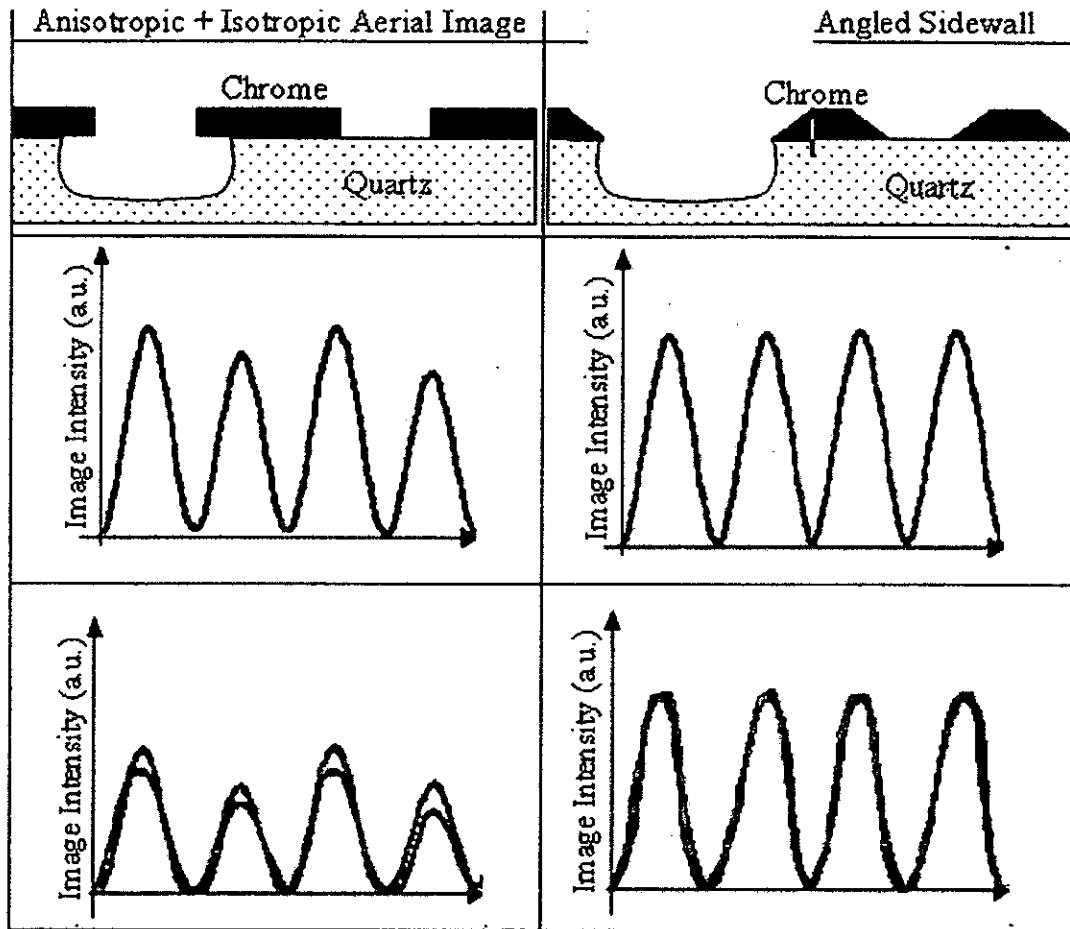


FIGURE 6C

FIGURE 6D

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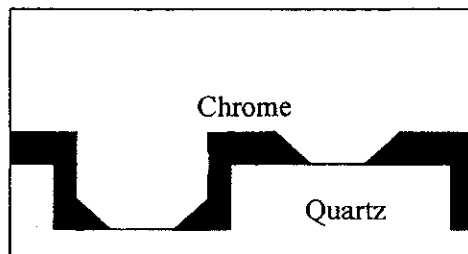


FIGURE 7A

SSCAAM: Sloped Sidewall Chrome Alternating Aperture Mask

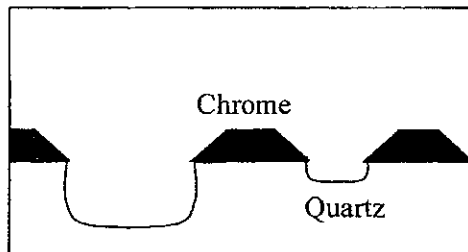


FIGURE 7B

Dual-trench Sloped Sidewall Chrome

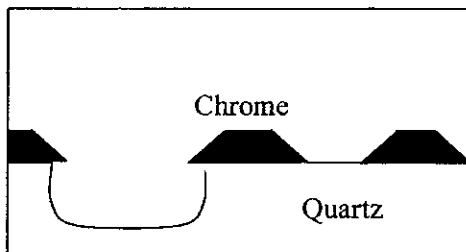


FIGURE 7C

Single-trench with undercut

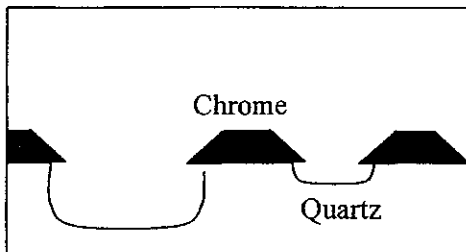


FIGURE 7D

Dual-trench Sloped Sidewall Chrome with undercut

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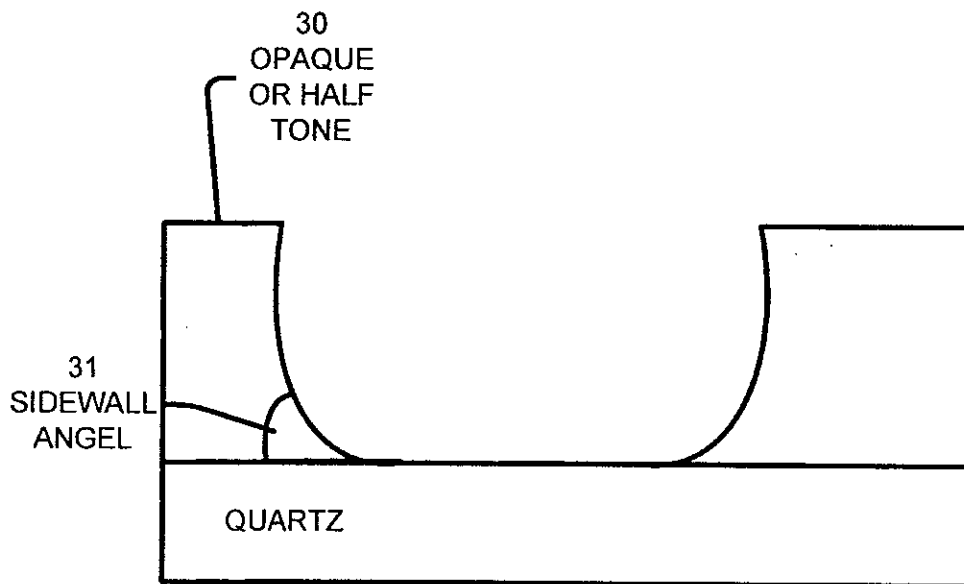


FIGURE 8A

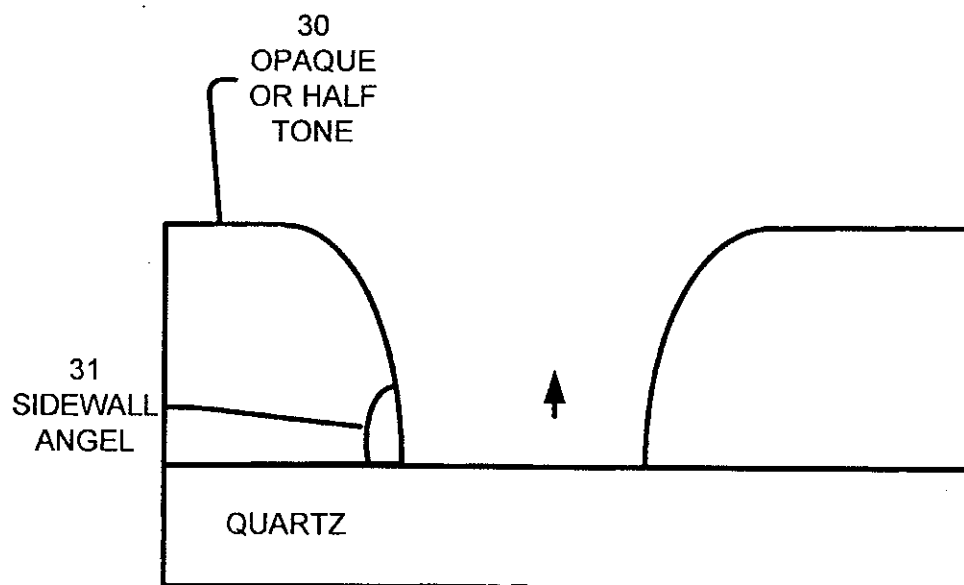


FIGURE 8B

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IMAGE IMBALANCE CORRECTION

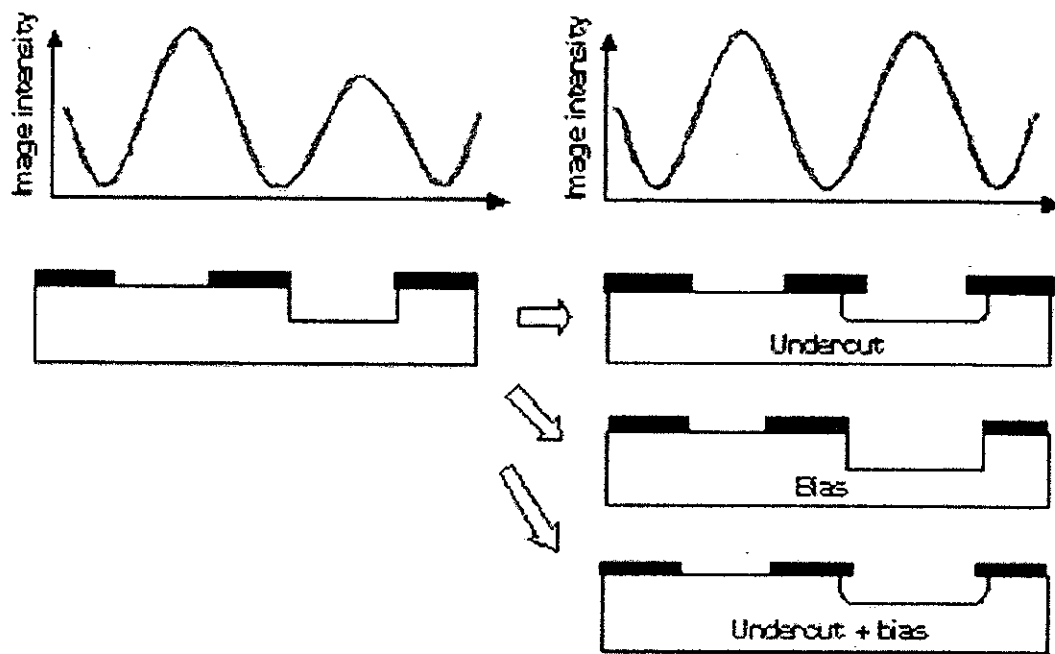


FIGURE 9 PRIOR ART